



PBSS5160T

60 V, 1 A PNP low V_{CEsat} (BISS) transistor

Rev. 04 — 15 January 2010

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4160T.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency due to less heat generation
- Reduces Printed-Circuit Board (PCB) area required
- Cost-effective replacement for medium power transistors BCP52 and BCX52

1.3 Applications

- Major application segments:
 - ◆ Automotive
 - ◆ Telecom infrastructure
 - ◆ Industrial
- Power management:
 - ◆ DC-to-DC conversion
 - ◆ Supply line switching
- Peripheral driver:
 - ◆ Driver in low supply voltage applications (e.g. lamps and LEDs)
 - ◆ Inductive load drivers (e.g. relays, buzzers and motors)

1.4 Quick reference data

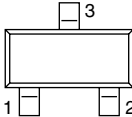
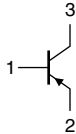
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current		-	-	-1	A
I_{CM}	peak collector current	$t = 1$ ms or limited by $T_{j(max)}$	-	-	-2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1$ A; $I_B = -100$ mA	[1] -	220	330	m Ω

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		
3	collector		

006aab25

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5160T	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS5160T	*U6

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

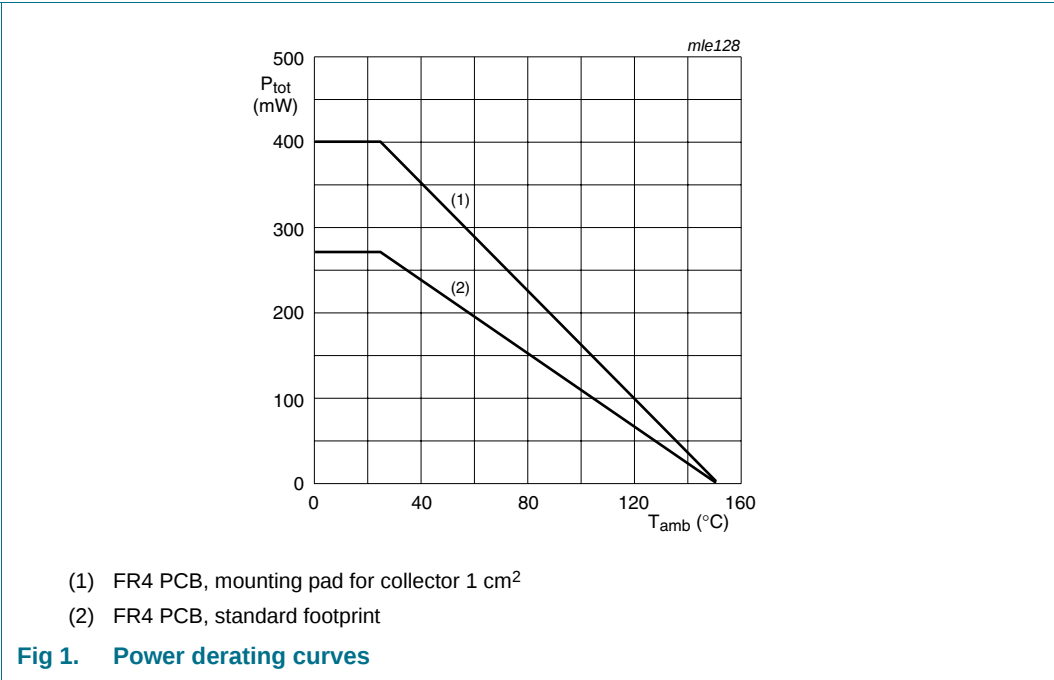
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-80	V
V_{CEO}	collector-emitter voltage	open base	-	-60	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current	^[1]	-	-0.9	A
		^[2]	-	-1	A
I_{CM}	peak collector current	$t = 1$ ms or limited by $T_{j(max)}$	-	-2	A
I_B	base current		-	-300	mA
I_{BM}	peak base current	$t_p \leq 300 \mu s$; $\delta \leq 0.02$	-	-1	A

Table 5. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	[1]	-	270 mW
			[2]	-	400 mW
			[1][3]	-	1.25 W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature		-65	+150	$^{\circ}\text{C}$
T_{stg}	storage temperature		-65	+150	$^{\circ}\text{C}$

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
[3] Operated under pulse conditions: duty cycle $\delta \leq 20\%$, pulse width $t_p \leq 10\text{ ms}$.

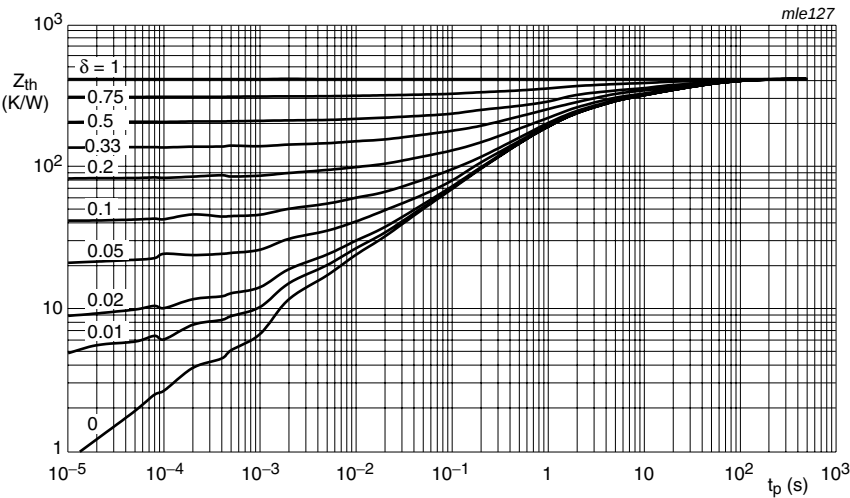


6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	465	K/W
			[2] -	-	312	K/W
			[1][3] -	-	100	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
[3] Operated under pulse conditions: duty cycle $\delta \leq 20\%$, pulse width $t_p \leq 10$ ms.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance as a function of pulse duration; typical values

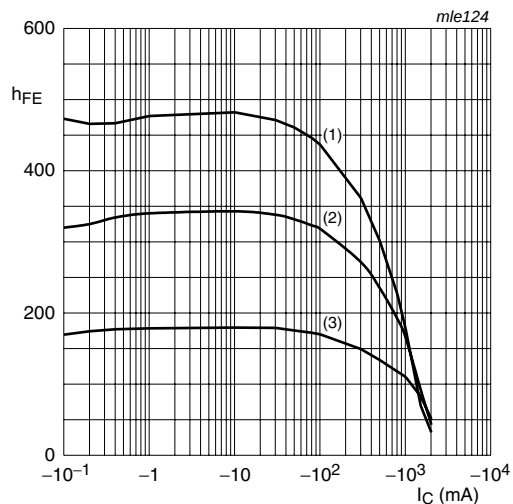
7. Characteristics

Table 7. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -60\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -60\text{ V}; V_{BE} = 0\text{ V}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}$				
		$I_C = -1\text{ mA}$	200	350	-	
		$I_C = -500\text{ mA}$	[1] 150	250	-	
		$I_C = -1\text{ A}$	[1] 100	160	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-110	-160	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-120	-175	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	-220	-330	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	220	330	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	-	-0.95	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	-	-0.82	-0.9	V
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	220	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	9	15	pF

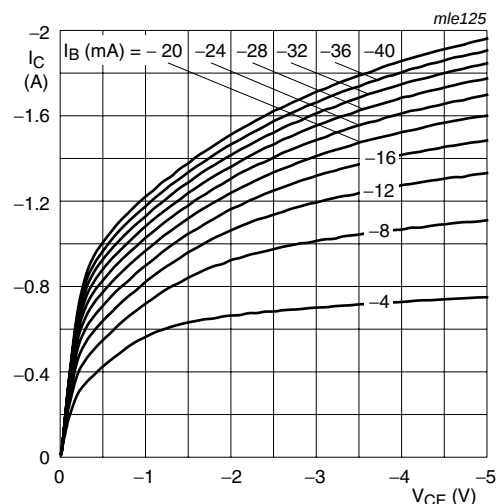
[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



$V_{CE} = -5 \text{ V}$

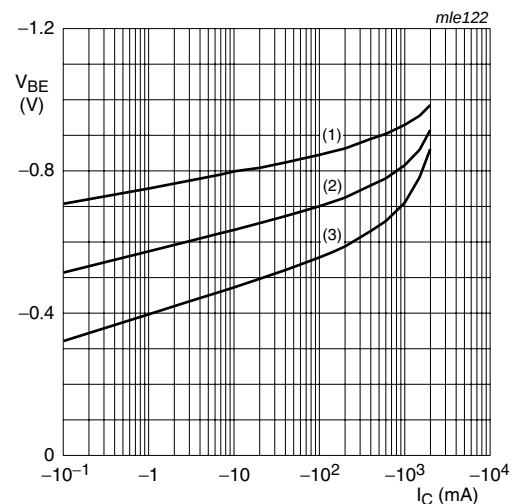
- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$

Fig 3. DC current gain as a function of collector current; typical values



$T_{amb} = 25 \text{ }^{\circ}\text{C}$

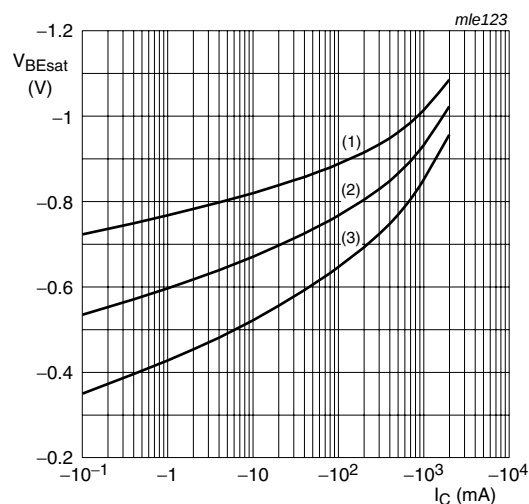
Fig 4. Collector current as a function of collector-emitter voltage; typical values



$V_{CE} = -5 \text{ V}$

- (1) $T_{amb} = -55 \text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$

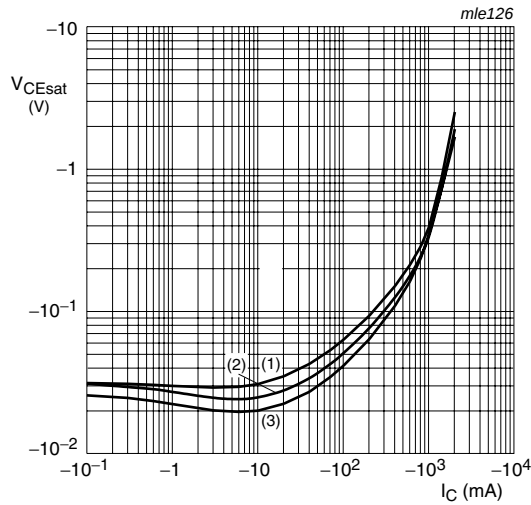
Fig 5. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$

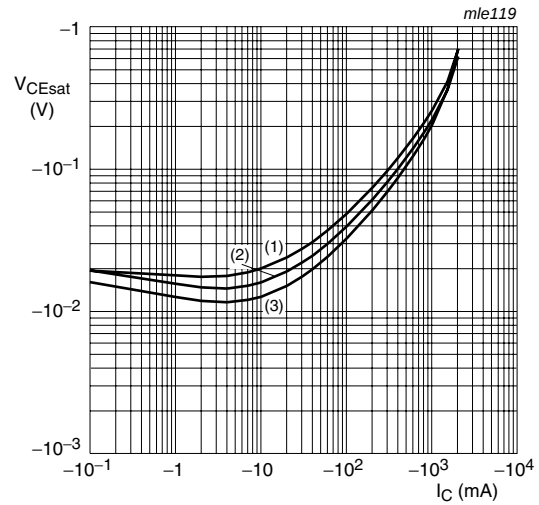
- (1) $T_{amb} = -55 \text{ }^{\circ}\text{C}$
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$
- (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values



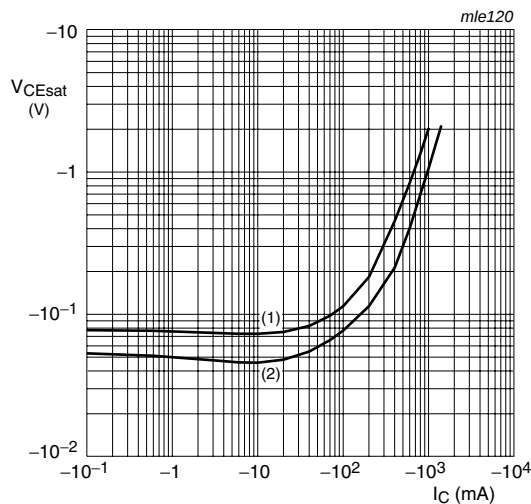
- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



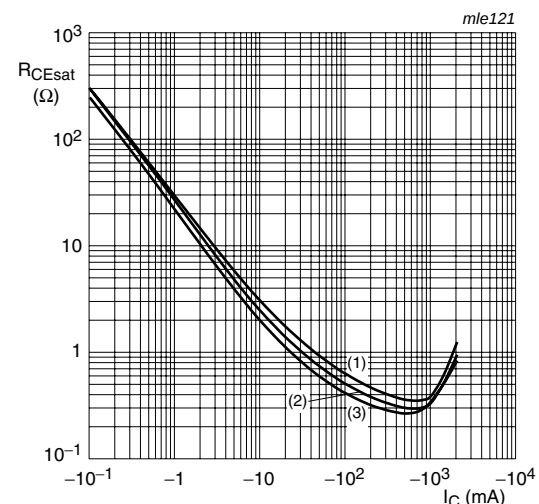
- $I_C/I_B = 10$
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1) $I_C/I_B = 100$
 - (2) $I_C/I_B = 50$

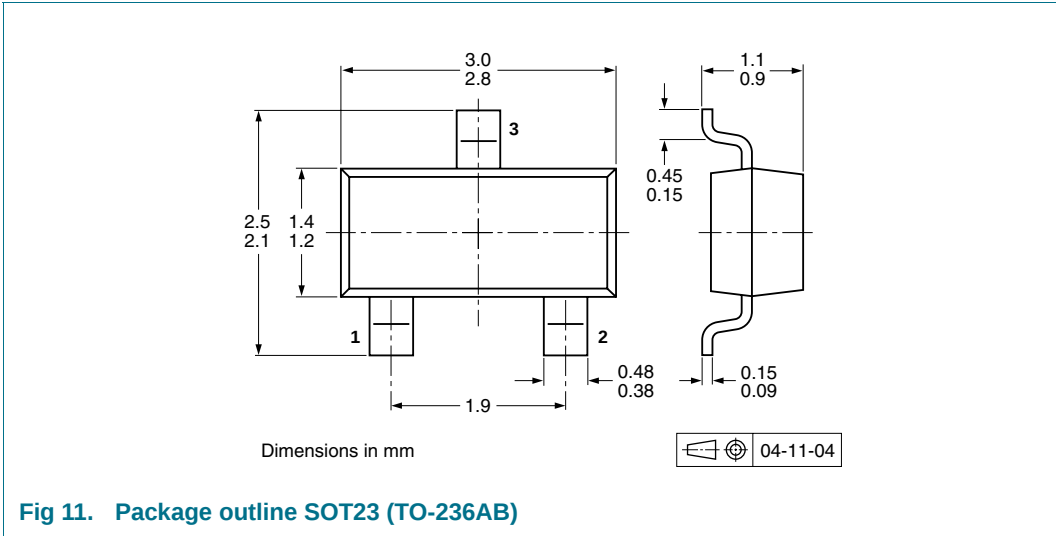
Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS5160T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see [Section 12](#).

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5160T_4	20100115	Product data sheet	-	PBSS5160T_N_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 1 "Quick reference data": amended • Section 4 "Marking": amended • Figure 4: updated • Figure 11: superseded by minimized package outline drawing • Section 9 "Packing information": added • Section 11 "Legal information": updated			
PBSS5160T_N_3	20080718	Product data sheet	-	PBSS5160T_2
PBSS5160T_2	20040527	Product specification	-	PBSS5160T_1
PBSS5160T_1	20030623	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

11.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

11.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nexperia.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by Nexperia. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

12. Contact information

For more information, please visit: <http://www.nexperia.com>

For sales office addresses, please send an email to: salesaddresses@nexperia.com

13. Contents

1 Product profile 1

1.1 General description 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data 1

2 Pinning information. 2

3 Ordering information. 2

4 Marking 2

5 Limiting values. 2

6 Thermal characteristics 4

7 Characteristics. 5

8 Package outline 8

9 Packing information 8

10 Revision history. 9

11 Legal information. 10

11.1 Data sheet status 10

11.2 Definitions 10

11.3 Disclaimers 10

11.4 Trademarks. 10

12 Contact information. 10

13 Contents 11

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9